74LVTN16245B

3.3 V 16-bit transceiver; 3-state

Rev. 5 — 5 April 2012

Product data sheet

1. General description

The 74LVTN16245B is a high-performance BiCMOS product designed for V_{CC} operation at 3.3 V.

This device is a 16-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The control function implementation minimizes external timing requirements. The device features an output enable input (nOE) for easy cascading and a direction input (nDIR) for direction control.

2. Features and benefits

- 16-bit bus interface
- 3-state buffers
- Output capability: +64 mA and -32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Power-up 3-state
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Latch-up protection
 - ◆ JESD78B Class II exceeds 500 mA
- ESD protection:
 - ♦ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V

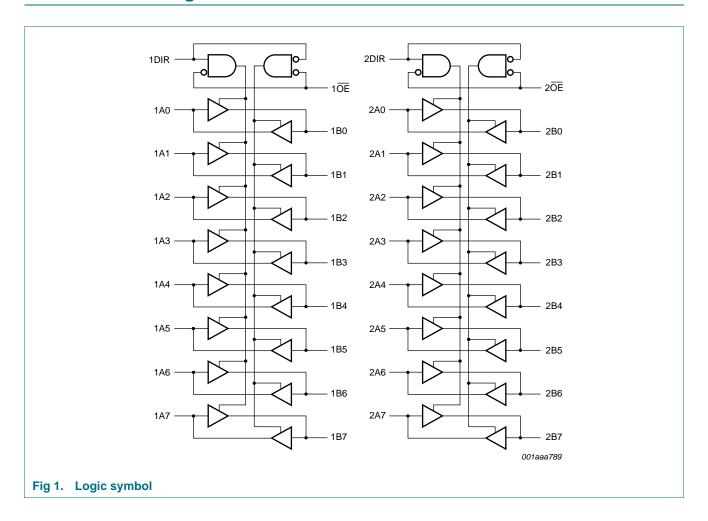
Ordering information

Table 1. **Ordering information**

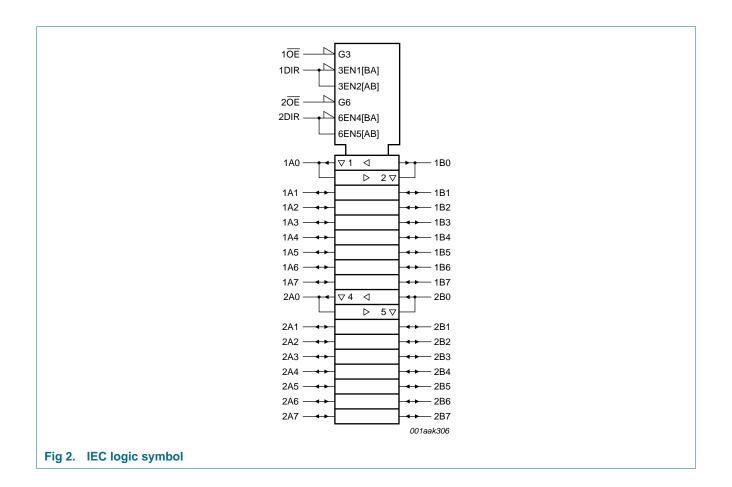
Type number	Package									
	Temperature range	Name	Description	Version						
74LVTN16245BDGG	-40 °C to +85 °C	TSSOP48	plastic thin shrink small outline package; 48 leads; body width 6.1 mm	SOT362-1						
74LVTN16245BBX	–40 °C to +125 °C	HXQFN60	plastic compatible thermal enhanced extremely thin quad flat package; no leads; 60 terminals; body 4 \times 6 \times 0.5 mm	SOT1134-2						



4. Functional diagram



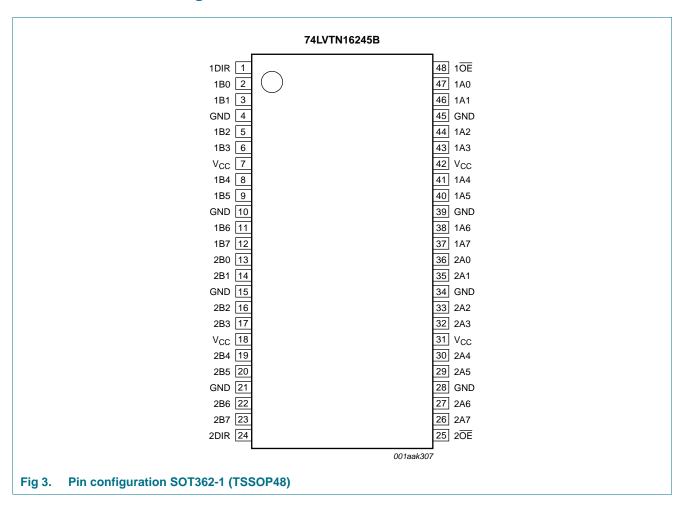
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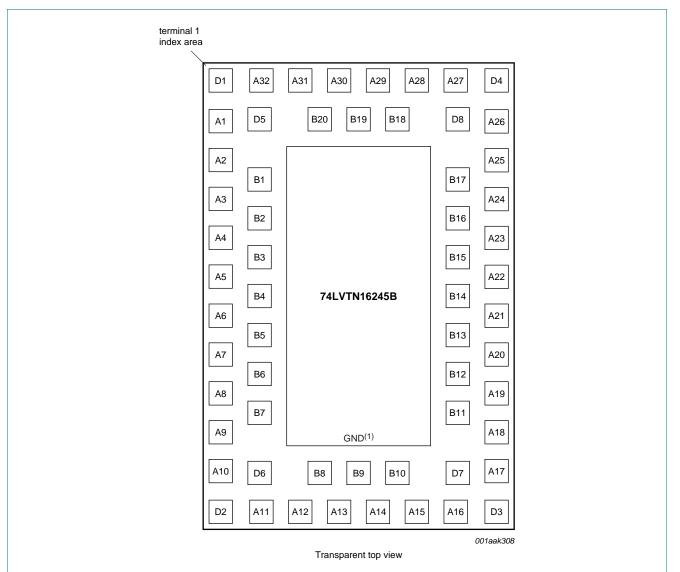
5. Pinning information

5.1 Pinning



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(1) This is not a supply pin, the substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad however if it is soldered the solder land should remain floating or be connected to GND.

Fig 4. Pin configuration SOT1134-2 (HXQFN60)

5.2 Pin description

Table 2. Pin description

Symbol	Pin		Description
	SOT362-1	SOT1134-2	·
1DIR, 2DIR	1, 24	A30, A13	direction control input
1B0 to 1B7	2, 3, 5, 6, 8, 9, 11, 12	B20, A31, D5, D1, A2, B2, B3, A5	data input/output
2B0 to 2B7	13, 14, 16, 17, 19, 20, 22, 23	A6, B5, B6, A9, D2, D6, A12, B8	data input/output
GND	4, 10, 15, 21, 28, 34, 39, 45	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)
V _{CC}	7, 18, 31, 42	A1, A10, A17, A26	supply voltage
10E, 20E	48, 25	A29, A14	output enable input (active LOW)
2A0 to 2A7	36, 35, 33, 32, 30, 29, 27, 26	A21, B13, B12, A18, D3, D7, A15, B10	data input/output
1A0 to 1A7	47, 46, 44, 43, 41, 40, 38, 37	B18, A28, D8, D4, A25, B16, B15, A22	data input/output
n.c.	-	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected

6. Functional description

Table 3. Function table [1]

Control		Input/output				
nOE	nDIR	nAn	nBn			
L	L	output nAn = nBn	input			
L	Н	input	output nBn = nAn			
Н	X	Z	Z			

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
V _I	input voltage		<u>[1]</u> –0.5	+7.0	V
V _O	output voltage	output in OFF-state or HIGH-state	<u>[1]</u> –0.5	+7.0	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
I _O	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-64	-	mA
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		[2] _	150	°C

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Product data sheet

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +85 ^{\circ}\text{C}$			
		TSSOP48 package	[3]	500	mW
		HXQFN60 package	<u>[4]</u> _	1000	mW

^[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		2.7	-	3.6	V
VI	input voltage		0	-	5.5	V
V_{IH}	HIGH-level input voltage		2.0	-	-	V
V_{IL}	LOW-level input voltage		-	-	8.0	V
I _{OH}	HIGH-level output current		-32	-	-	mA
I _{OL}	LOW-level output current	none	-	-	32	mA
		current duty cycle \leq 50 %; $f_i \geq$ 1 kHz	-	-	64	mA
T _{amb}	ambient temperature	in free-air	-40	-	+85	°C
Δt/ΔV	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

	, ,	, ,	,			
Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T _{amb} = -	40 °C to +85 °C					
V_{IK}	input clamping voltage	$V_{CC} = 2.7 \text{ V}; I_{IK} = -18 \text{ mA}$	-1.2	-0.85	-	V
V _{OH}	HIGH-level output voltage	I_{OH} = $-100 \mu A$; V_{CC} = 2.7 V to 3.6 V	$V_{CC}-0.2$	V_{CC}	-	V
		$I_{OH} = -8 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.4	2.5	-	V
V _{OL} LO		$I_{OH} = -32 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	2.3	-	V
V _{OL} Lo	LOW-level output voltage	V _{CC} = 2.7 V				
		I _{OL} = 100 μA	-	0.07	0.2	V
		I _{OL} = 24 mA	-	0.3	0.5	V
		V _{CC} = 3.0 V				
		I _{OL} = 16 mA	-	0.25	0.4	V
		I _{OL} = 32 mA	-	0.3	0.5	V
		I _{OL} = 64 mA	-	0.4	0.55	V

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^[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

^[3] Above 60 $^{\circ}$ C the value of P_{tot} derates linearly with 5.5 mW/K.

^[4] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

Table 6. Static characteristics ... continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
I _I	input leakage current	control pins				
		$V_{CC} = 3.6 \text{ V}; V_I = V_{CC} \text{ or GND}$	-	0.1	±1	μΑ
		$V_{CC} = 0 \text{ V or } 3.6 \text{ V}; V_{I} = 5.5 \text{ V}$	-	0.1	10	μΑ
		input/output data pins; V _{CC} = 3.6 V	[2]			
		V _I = 5.5 V	-	0.1	20	μΑ
		$V_I = V_{CC}$	-	0.5	10	μΑ
		V _I = 0 V	-5	-0.1	-	μΑ
l _{OFF}	power-off leakage current	$V_{CC} = 0 \text{ V}$; $V_I \text{ or } V_O = 0 \text{ V to } 4.5 \text{ V}$	-	0.1	±100	μΑ
I _{LO}	output leakage current	output in HIGH-state when $V_O > V_{CC}$; $V_O = 5.5 \text{ V}$; $V_{CC} = 3.0 \text{ V}$	-	75	125	μА
I _{O(pu/pd)}	power-up/power-down output current	$V_{CC} \le 1.2 \text{ V}; V_O = 0.5 \text{ V} \text{ to } V_{CC};$ $V_I = \text{GND or } V_{CC}; n\overline{OE} = \text{don't care}$	[3] _	40	±100	μА
Icc	supply current	V_{CC} = 3.6 V; V_I = GND or V_{CC} ; I_O = 0 A				
		output HIGH	-	0.07	0.12	mΑ
		output LOW	-	4.0	6.0	mΑ
		outputs disabled	[4] _	0.07	0.12	mA
Δl _{CC}	additional supply current	per input pin; V_{CC} = 3.0 V to 3.6 V; one input at V_{CC} – 0.6 V other inputs at V_{CC} or GND	<u>[5]</u> _	0.1	0.2	mA
Cı	input capacitance	pins nDIR and n \overline{OE} , V _O = 0 V or 3.0 V	-	3	-	pF
$C_{io(off)}$	off-state input/output capacitance	pins nAn and nBn, outputs disabled; $V_O = GND$ or V_{CC}	-	9	-	pF

^[1] Typical values are measured at V_{CC} = 3.3 V and at T_{amb} = 25 °C.

^[2] Unused pins at V_{CC} or GND.

^[3] This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.3 V \pm 0.3 V a transition time of 100 μ s is permitted. This parameter is valid for T_{amb} = 25 °C only.

^[4] I_{CC} is measured with outputs pulled to V_{CC} or GND.

^[5] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

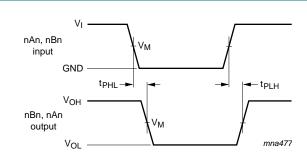
Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
$T_{amb} = -40$	°C to +85 °C					
t _{PLH}	LOW to HIGH propagation delay	nAn to nBn or nBn to nAn; see Figure 5				
		V _{CC} = 2.7 V	-	-	3.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	1.9	3.5 ns 1.9 3.3 ns 1.7 3.3 ns 2.8 4.5 ns 2.8 4.1 ns 5.7 ns	ns
t _{PHL}	HIGH to LOW propagation delay	nAn to nBn or nBn to nAn; see Figure 5				
		V _{CC} = 2.7 V	-	-	3.5	ns
		V _{CC} = 3.0 V to 3.6 V	on nBn or nBn to nAn; gure 5 = 2.7 V	1.7	3.3	ns
1 411	OFF-state to HIGH propagation delay	nOE to nAn or nBn; see <u>Figure 6</u>				
		V _{CC} = 2.7 V	-	-	5.3	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.8	4.5	ns
1 44	OFF-state to LOW propagation delay	nOE to nAn or nBn; see Figure 6				
		V _{CC} = 2.7 V	-	-	5.1	ns
tpHL F p ttpZH C p ttpZL C p ttpHZ F p		V _{CC} = 3.0 V to 3.6 V	1.0	2.8	4.1	ns
t _{PHZ}	HIGH to OFF-state propagation delay	nOE to nAn or nBn; see <u>Figure 6</u>				
		V _{CC} = 2.7 V	-	-	5.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.5	3.2	5.1	ns
t _{PLZ}	LOW to OFF-state propagation delay	nOE to nAn or nBn; see <u>Figure 6</u>				
		$V_{CC} = 2.7 \text{ V}$	-	-	4.6	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.5	3.0	4.6	ns

^[1] Typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

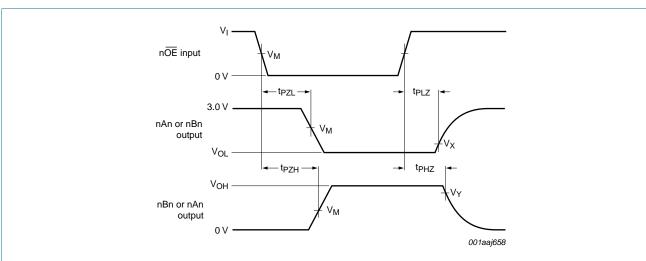
11. Waveforms



Measurements points are given in Table 8.

 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 5. Propagation delay input (nAn, nBn) to output (nBn, nAn)



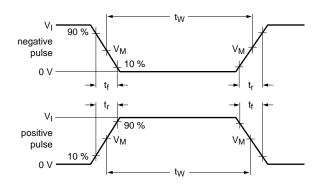
Measurements points are given in Table 8.

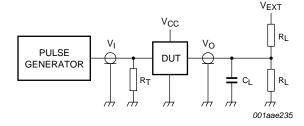
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Enable and disable times

Table 8. Measurement points

Input	Output		
V_{M}	V_{M}	V _X	V _Y
1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V





Test data is given in Table 9.

Definitions test circuit:

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 7. Test circuit for measuring switching times

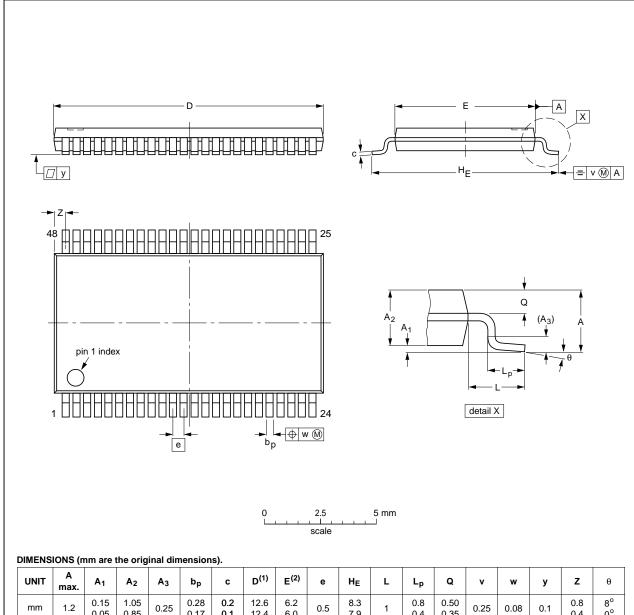
Table 9. Test data

Input			Load		V _{EXT}			
V_{I}	f_i t_W t_r , t_f		t _r , t _f	C _L R _L		t _{PHZ} , t _{PZH}	t_{PLZ}, t_{PZL}	t _{PLH} , t _{PHL}
2.7 V	≤ 10 MHz	500 ns	≤ 2.5 ns	50 pF	500Ω	GND	6 V	open

12. Package outline

TSSOP48: plastic thin shrink small outline package; 48 leads; body width 6.1 mm

SOT362-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z	θ
mm	1.2	0.15 0.05	1.05 0.85	0.25	0.28 0.17	0.2 0.1	12.6 12.4	6.2 6.0	0.5	8.3 7.9	1	0.8 0.4	0.50 0.35	0.25	0.08	0.1	0.8 0.4	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT362-1		MO-153				99-12-27 03-02-19

Fig 8. Package outline SOT362-1 (TSSOP48)

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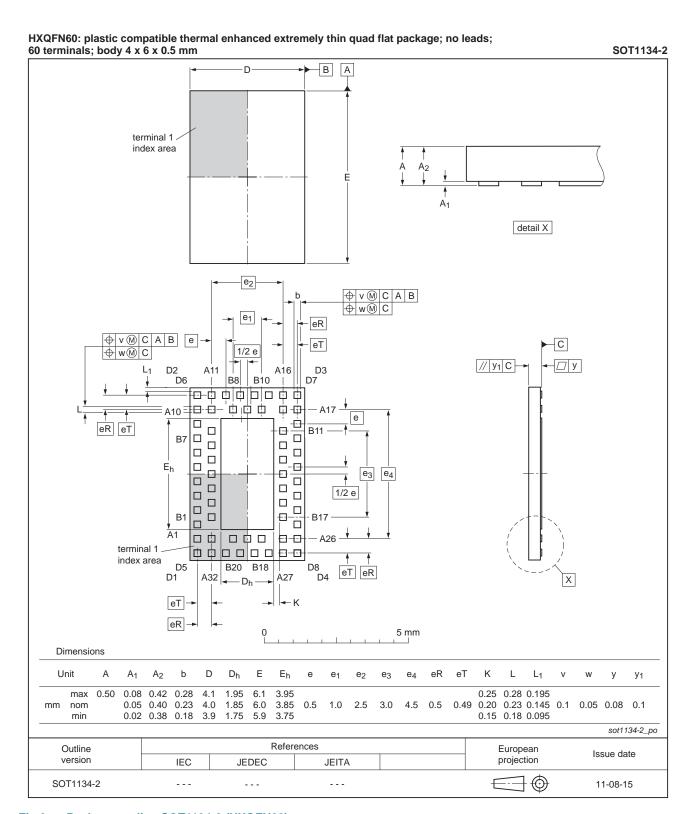


Fig 9. Package outline SOT1134-2 (HXQFN60)

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
BiCMOS	Bipolar Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVTN16245B v.5	20120405	Product data sheet	-	74LVTN16245B v.4
Modifications:	 For type nu 	mber 74LVTN16245BBX th	ne SOT code has change	ed to SOT1134-2
74LVTN16245B v.4	20111122	Product data sheet	-	74LVTN16245B v.3
Modifications:	 Legal pages 	s updated.		
74LVTN16245B v.3	20110615	Product data sheet	-	74LVTN16245B v.2
74LVTN16245B v.2	20100323	Product data sheet	-	74LVTN16245B v.1
74LVTN16245B v.1	20090729	Product data sheet	-	-

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15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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